

Listing of Claims:

This listing of claims replaces all prior versions and listings of claims in the application.

1. (Currently amended) A semiconductor device comprising:
a source, a gate and a drain;
a source-drain depletion region in a substrate under the gate;
a single deep-pocket ion implant and a single shallow-pocket ion implant provided in the source-drain depletion region in a staggered configuration, wherein the semiconductor device contains only one deep-pocket ion implant and only one shallow-pocket ion implant at a drain side; and
~~a single shallow-pocket ion implant in the source-drain depletion region at a source side.~~
2. - 14. (Previously canceled)
15. (Previously amended) The semiconductor device as recited in claim 1, further comprising:
a secondary deep-pocket ion implant in a source side of the source-drain depletion region, the secondary deep-pocket ion implant having been countered by ions of the source; and
a secondary shallow-pocket ion implant in a drain side of the source-drain depletion region, the secondary shallow-pocket ion implant having been countered by ions of the drain.
16. - 21. (Previously canceled)
22. (Canceled)

23. (New) The semiconductor device of claim 1, wherein the single deep-pocket ion implant is in the source-drain depletion region is at a drain side and the single shallow-pocket ion implant in the source-drain depletion region is at a source side.

24. (New) The semiconductor device of claim 1, wherein the single deep-pocket ion implant is in the source-drain depletion region is at a source side and the single shallow-pocket ion implant in the source-drain depletion region is at a drain side.

25. (New) A semiconductor device comprising:

a source, a gate and a drain;
a source-drain depletion region in a substrate under the gate;
a single deep-pocket ion implant in the source-drain depletion region at a drain side;
a single shallow-pocket ion implant in the source-drain depletion region at a source side;
a secondary deep-pocket ion implant in a source side of the source-drain depletion region, the secondary deep-pocket ion implant having been countered by ions of the source; and
a secondary shallow-pocket ion implant in a drain side of the source-drain depletion region, the secondary shallow-pocket ion implant having been countered by ions of the drain.

26. (New) A semiconductor device comprising:

a source, a gate and a drain;
a source-drain depletion region in a substrate under the gate;
a single deep-pocket ion implant in the source-drain depletion region at a source side;
a single shallow-pocket ion implant in the source-drain depletion region at a drain side;
a secondary deep-pocket ion implant in a drain side of the source-drain depletion region, the secondary deep-pocket ion implant having been countered by ions of the drain; and
a secondary shallow-pocket ion implant in a source side of the source-drain depletion region, the secondary shallow-pocket ion implant having been countered by ions of the source.